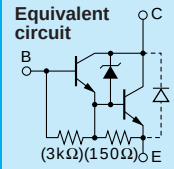


Built-in Avalanche Diode
for Surge Absorbing

达林顿796"供应商

2SD1796



Silicon NPN Triple Diffused Planar Transistor

Application : Driver for Solenoid, Relay and Motor and General Purpose

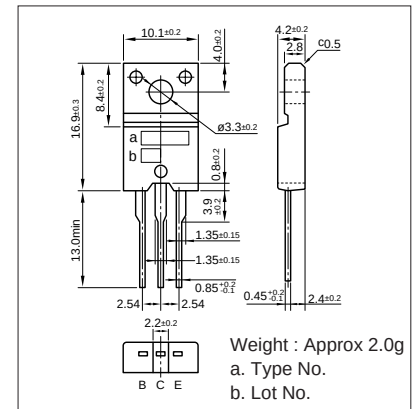
Absolute maximum ratings (Ta=25°C)

Symbol	2SD1796	Unit
VCBO	60±10	V
VCEO	60±10	V
VEBO	6	V
IC	4	A
IB	0.5	A
Pc	25(Tc=25°C)	W
Tj	150	°C
Tstg	-55 to +150	°C

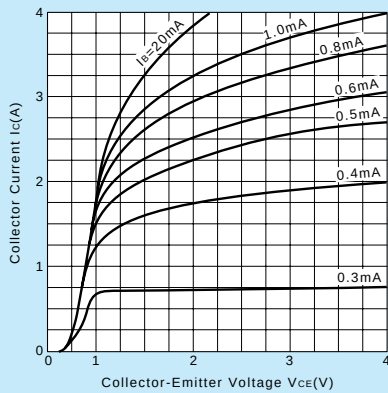
Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SD1796	Unit
ICBO	VCB=50V	10max	μA
IEBO	VEB=6V	10max	mA
V(BR)CEO	IC=10mA	60±10	V
hFE	VCE=4V, IC=3A	2000min	
VCE(sat)	IC=3A, IB=10mA	1.5max	V
fT	VCE=12V, IE=-0.2A	60typ	MHz
COB	VCB=10V, f=1MHz	45 typ	pF

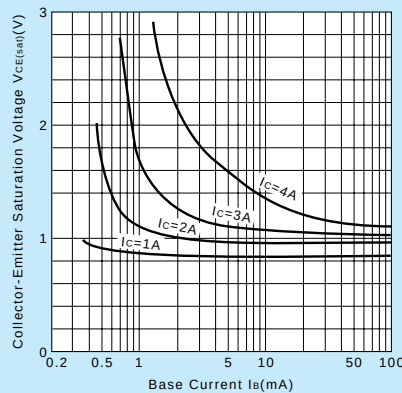
External Dimensions FM20(TO220F)



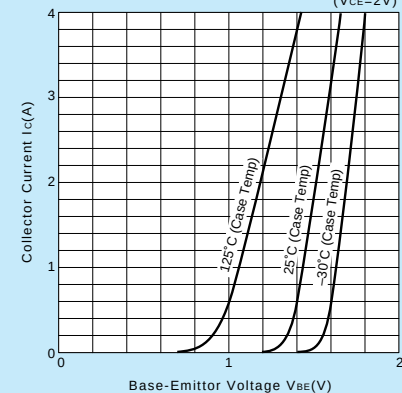
IC-VCE Characteristics (Typical)



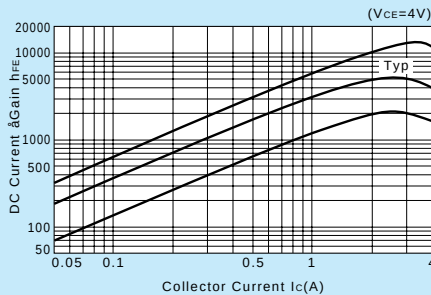
VCE(sat)-IB Characteristics (Typical)



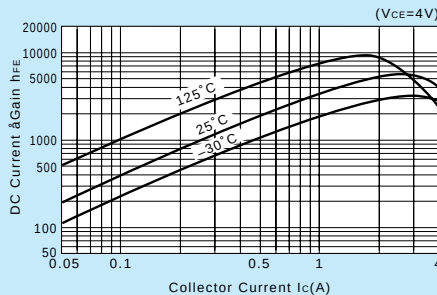
IC-VBE Temperature Characteristics (Typical)



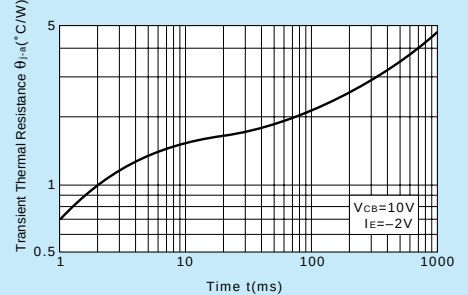
hFE-IC Characteristics (Typical)



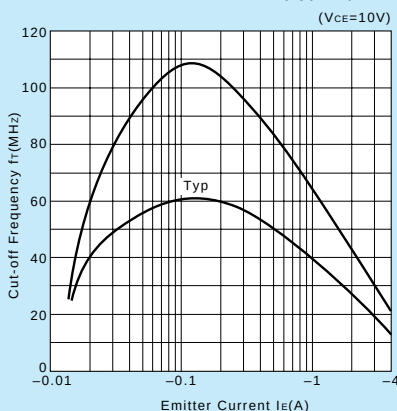
hFE-IC Temperature Characteristics (Typical)



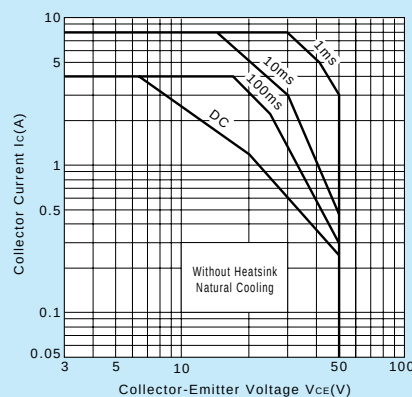
θJA-t Characteristics



fT-IE Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc-Ta Derating

